

Phase Control Thyristor

Preliminary Information

DS5830-1.3 June 2008 (LN26220)

FEATURES

- Double Side Cooling
- High Surge Capability

KEY PARAMETERS

V_{DRM}	5200V
$I_{T(AV)}$	690A
I_{TSM}	9450A
dV/dt^*	1500V/ μ s
dI/dt	300A/ μ s

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

* Higher dV/dt selections available

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages V_{DRM} and V_{RRM} V	Conditions
DCR690G52*	5200	$T_{vj} = -40^{\circ}\text{C}$ to 125°C , $I_{DRM} = I_{RRM} = 100\text{mA}$, $V_{DRM}, V_{RRM} t_p = 10\text{ms}$, $V_{DSM} \text{ \& } V_{RSM} =$ $V_{DRM} \text{ \& } V_{RRM} + 100\text{V}$ respectively
DCR690G50	5000	
DCR690G48	4800	

Lower voltage grades available.

* 5000V @ -40°C , 5200V @ 0°C

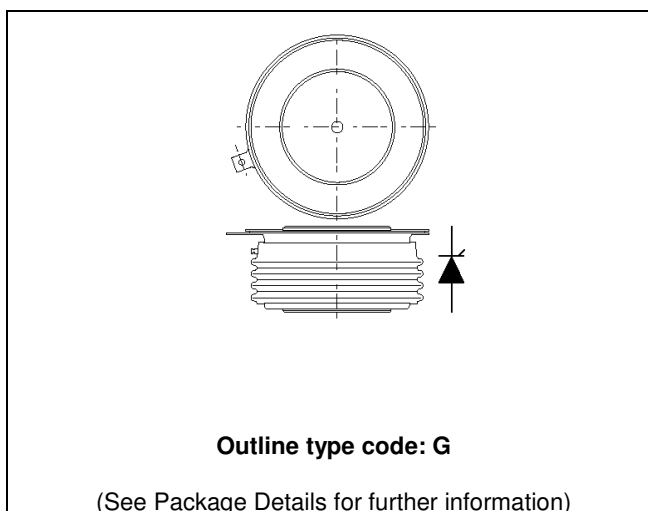


Fig. 1 Package outline

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR690G52

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

CURRENT RATINGS

$T_{case} = 60^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Side Cooled				
$I_{T(AV)}$	Mean on-state current	Half wave resistive load	690	A
$I_{T(RMS)}$	RMS value	-	1084	A
I_T	Continuous (direct) on-state current	-	1050	A

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
I_{TSM}	Surge (non-repetitive) on-state current	10ms half sine, $T_{case} = 125^{\circ}\text{C}$	9.45	kA
I^2t	I^2t for fusing	$V_R = 0$	0.45	MA^2s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
$R_{th(j-c)}$	Thermal resistance – junction to case	Double side cooled	DC	-	0.0268	$^{\circ}\text{C/W}$
		Single side cooled	Anode DC	-	0.0527	$^{\circ}\text{C/W}$
			Cathode DC	-	0.0652	$^{\circ}\text{C/W}$
$R_{th(c-h)}$	Thermal resistance – case to heatsink	Clamping force 11.5kN (with mounting compound)	Double side	-	0.0072	$^{\circ}\text{C/W}$
			Single side	-	.0144	$^{\circ}\text{C/W}$
T_{vj}	Virtual junction temperature	On-state (conducting)		-	135	$^{\circ}\text{C}$
		Reverse (blocking)		-	125	$^{\circ}\text{C}$
T_{stg}	Storage temperature range			-55	125	$^{\circ}\text{C}$
F_m	Clamping force			10	13	kN

DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
I _{RRM} /I _{DRM}	Peak reverse and off-state current	At V _{RRM} /V _{DRM} , T _{case} = 125 °C		-	100	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V _{DRM} , T _j = 125 °C, gate open		-	1500	V/μs
dI/dt	Rate of rise of on-state current	From 67% V _{DRM} to 2x I _{T(AV)}	Repetitive 50Hz	-	150	A/μs
		Gate source 30V, 10Ω, t _r < 0.5μs, T _j = 125 °C	Non-repetitive	-	300	A/μs
V _{T(TO)}	Threshold voltage – Low level	100A to 380A at T _{case} = 125 °C		-	.9	V
	Threshold voltage – High level	380A to 3000A at T _{case} = 125 °C		-	1.075	V
r _T	On-state slope resistance – Low level	100A to 380A at T _{case} = 125 °C		-	1.618	mΩ
	On-state slope resistance – High level	380A to 3000A at T _{case} = 125 °C		-	1.125	mΩ
t _{gd}	Delay time	V _D = 67% V _{DRM} , gate source 30V, 10Ω t _r = 0.5μs, T _j = 25 °C		-	3	μs
t _q	Turn-off time	T _j = 125 °C, V _R = 200V, dI/dt = 5A/μs, dV _{DR} /dt = 20V/μs linear		400	800	μs
Q _S	Stored charge	I _T = 2000A, T _j = 125 °C, dI/dt = 5A/μs,		1200	2400	μC
I _L	Latching current	T _j = 25 °C, V _D = 5V		-	3	A
I _H	Holding current	T _j = 25 °C, R _{G-K} = ∞, I _{TM} = 500A, I _T = 5A		-	300	mA

GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V_{GT}	Gate trigger voltage	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	1.5	V
V_{GD}	Gate non-trigger voltage	At 50% $V_{DRM}, T_{case} = 125^{\circ}C$	0.4	V
I_{GT}	Gate trigger current	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	250	mA
I_{GD}	Gate non-trigger current	At 50% $V_{DRM}, T_{case} = 125^{\circ}C$	15	mA

CURVES

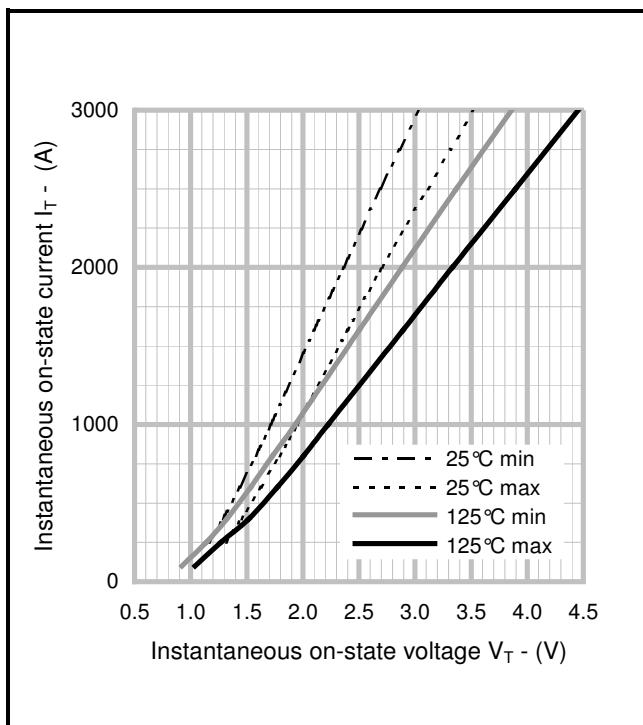


Fig.2 Maximum & minimum on-state characteristics

V_{TM} EQUATION

$$V_{TM} = A + B \ln(I_T) + C \cdot I_T + D \cdot \sqrt{I_T}$$

Where

$$\begin{aligned} A &= 0.246536 \\ B &= 0.166331 \\ C &= 0.001110 \\ D &= -0.008349 \end{aligned}$$

these values are valid for $T_j = 125^{\circ}C$ for I_T 50A to 3000A

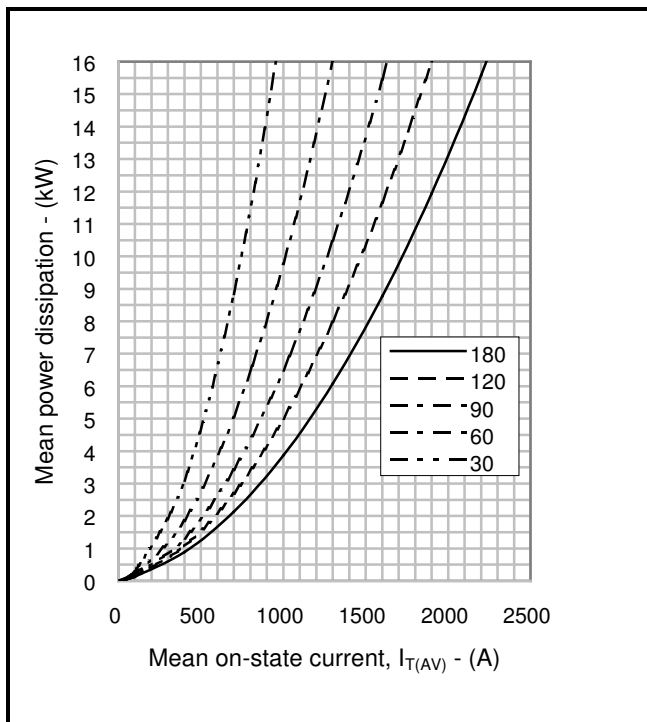


Fig.3 On-state power dissipation – sine wave

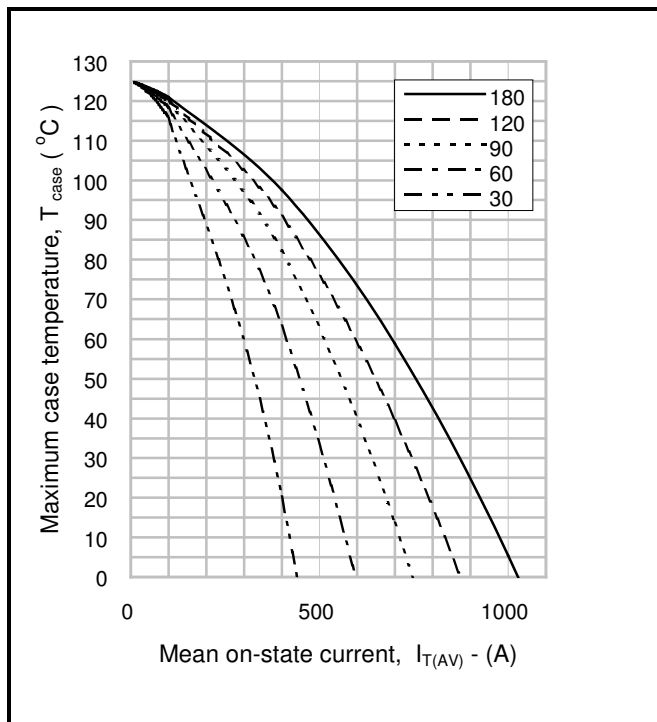


Fig.4 Maximum permissible case temperature, double side cooled – sine wave

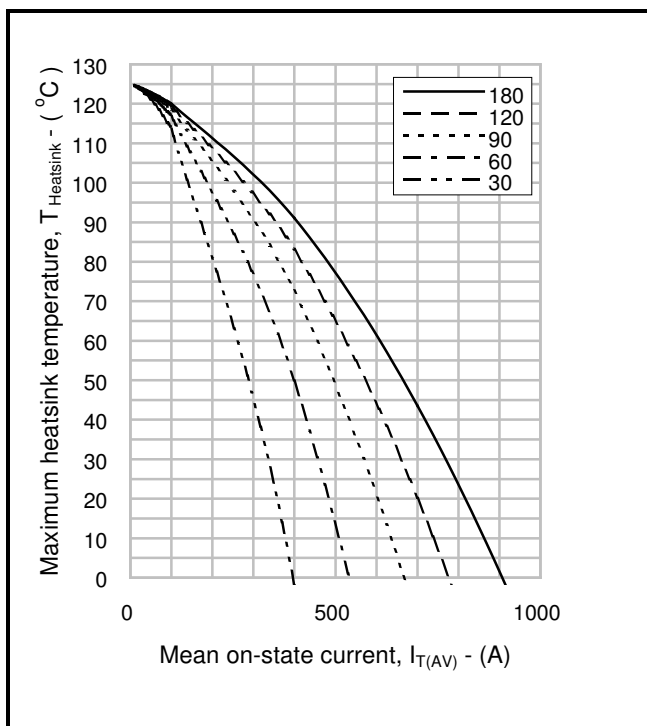


Fig.5 Maximum permissible heatsink temperature, double side cooled – sine wave

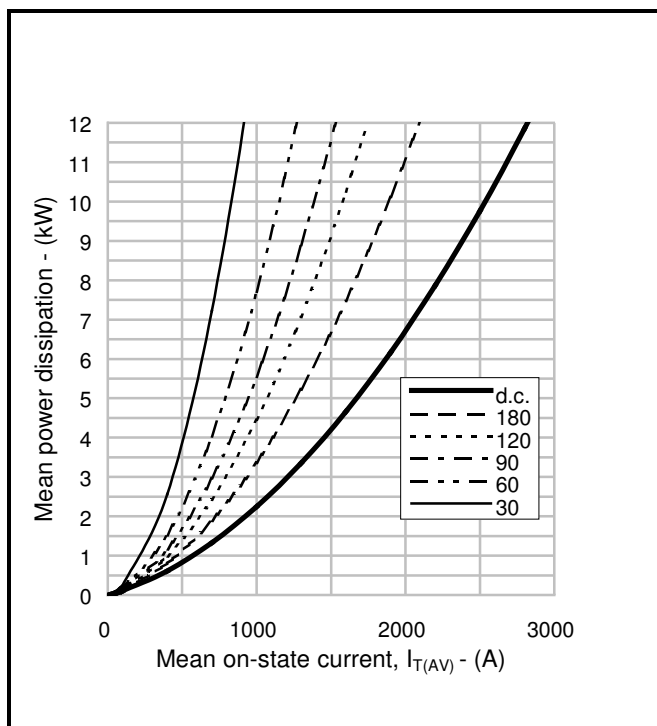


Fig.6 On-state power dissipation – rectangular wave

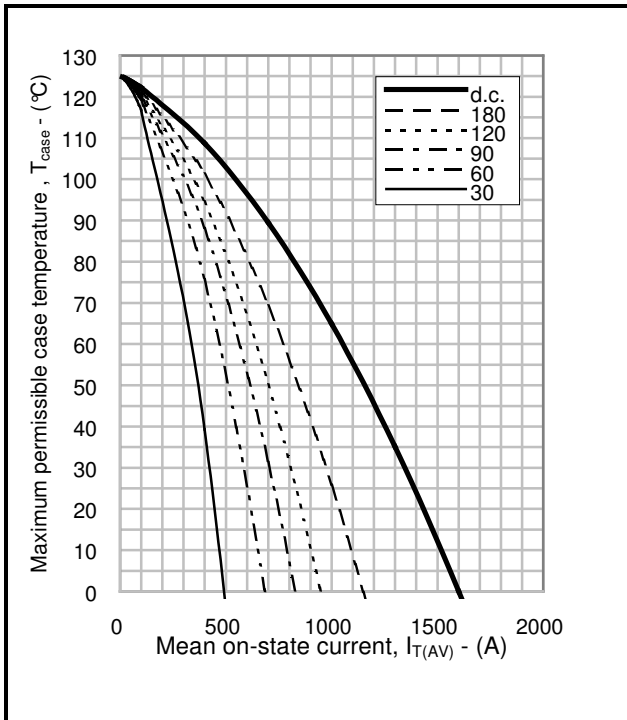


Fig.7 Maximum permissible case temperature, double side cooled – rectangular wave

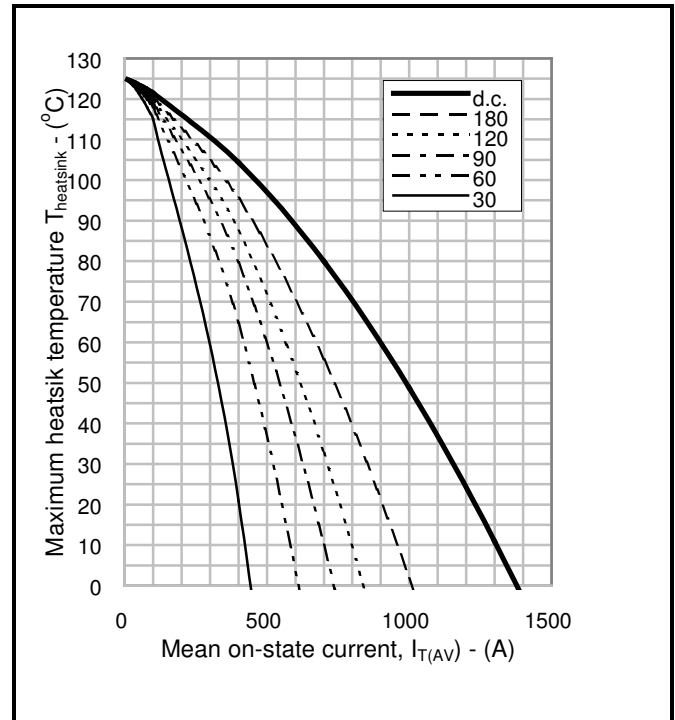


Fig.8 Maximum permissible heatsink temperature, double side cooled – rectangular wave

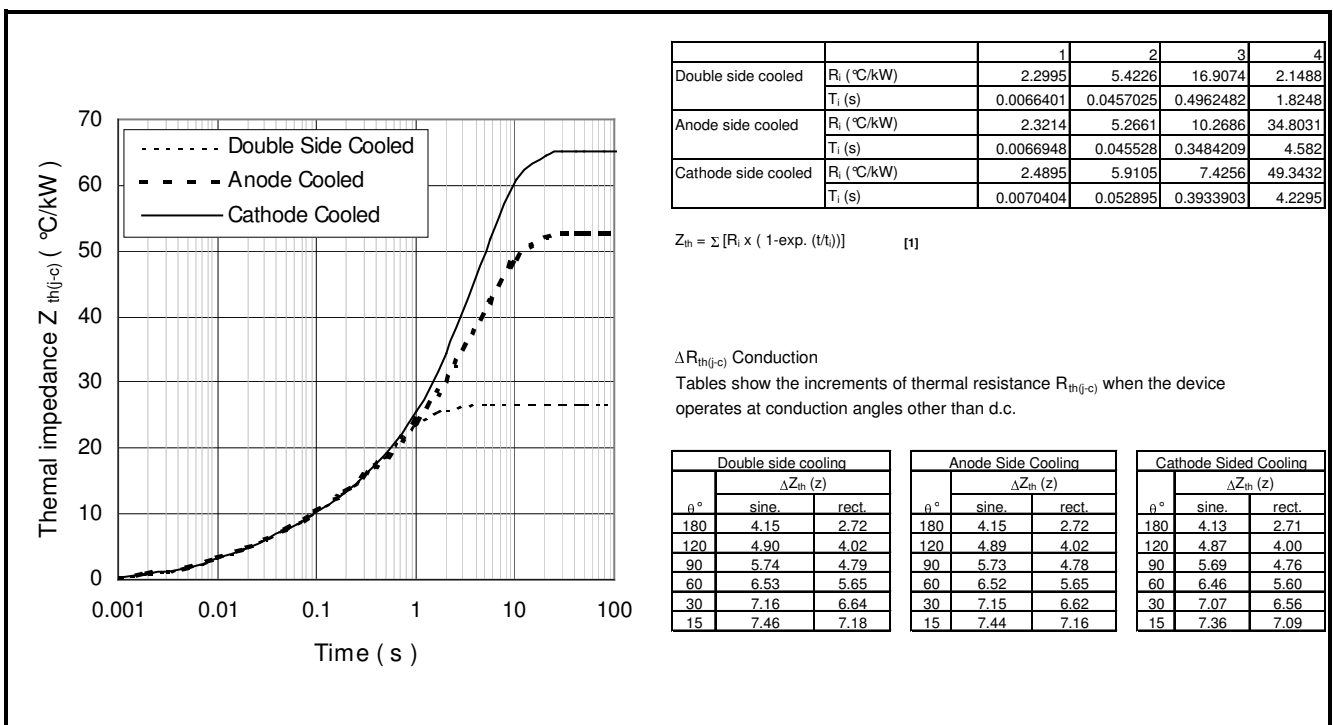


Fig.9 Maximum (limit) transient thermal impedance – junction to case (°C/kW)

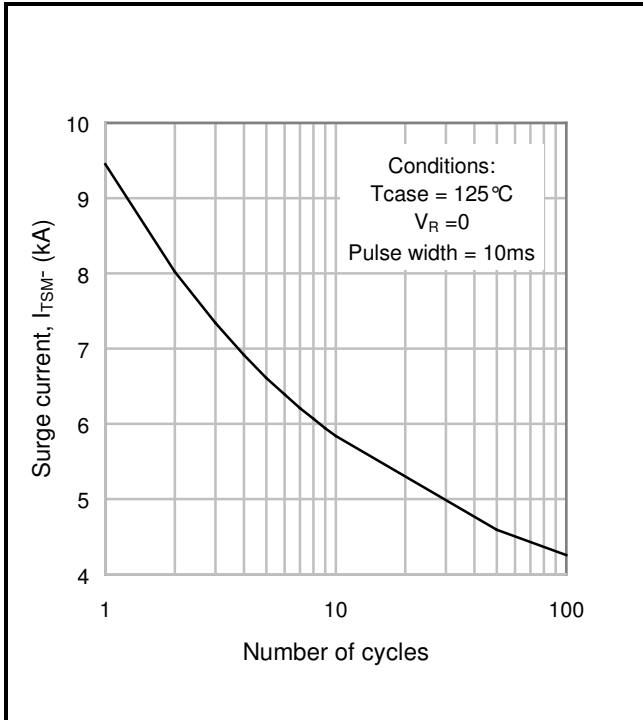


Fig.10 Multi-cycle surge current

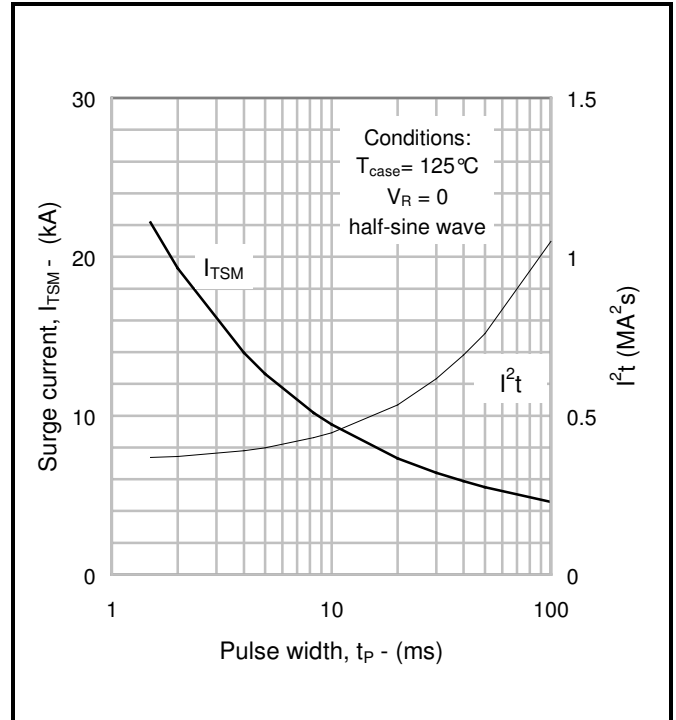


Fig.11 Single-cycle surge current

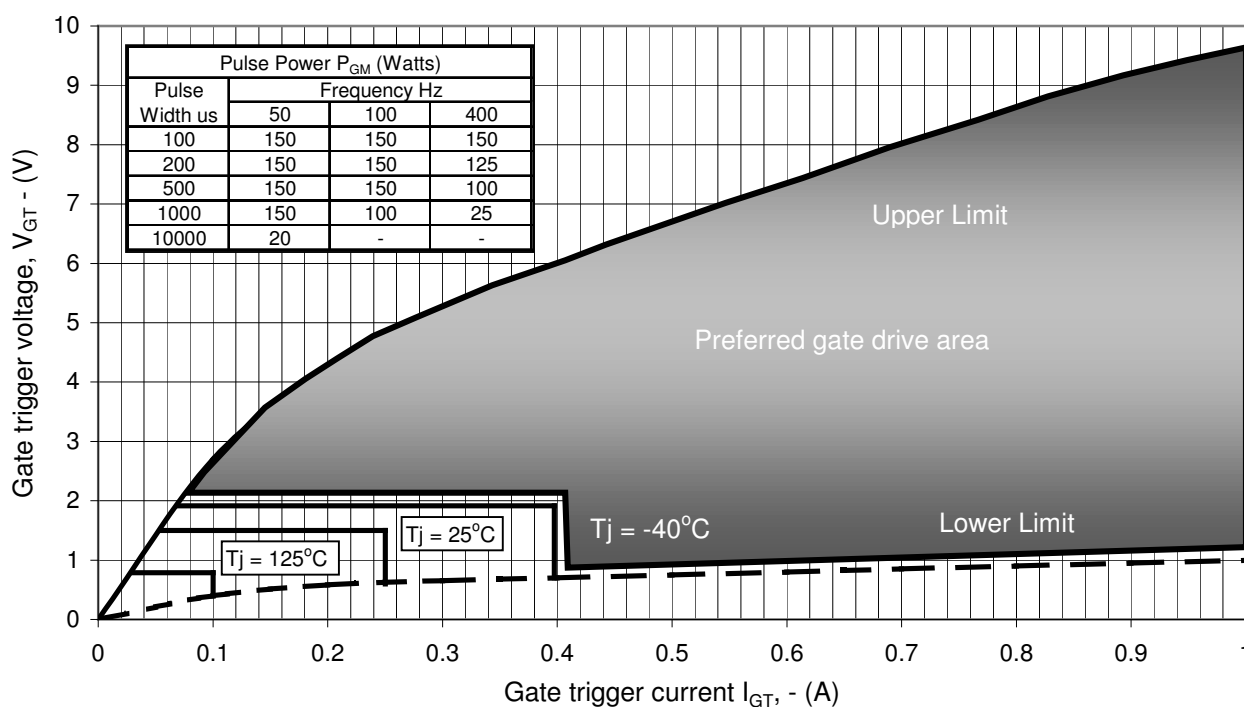


Fig12 Gate Characteristics

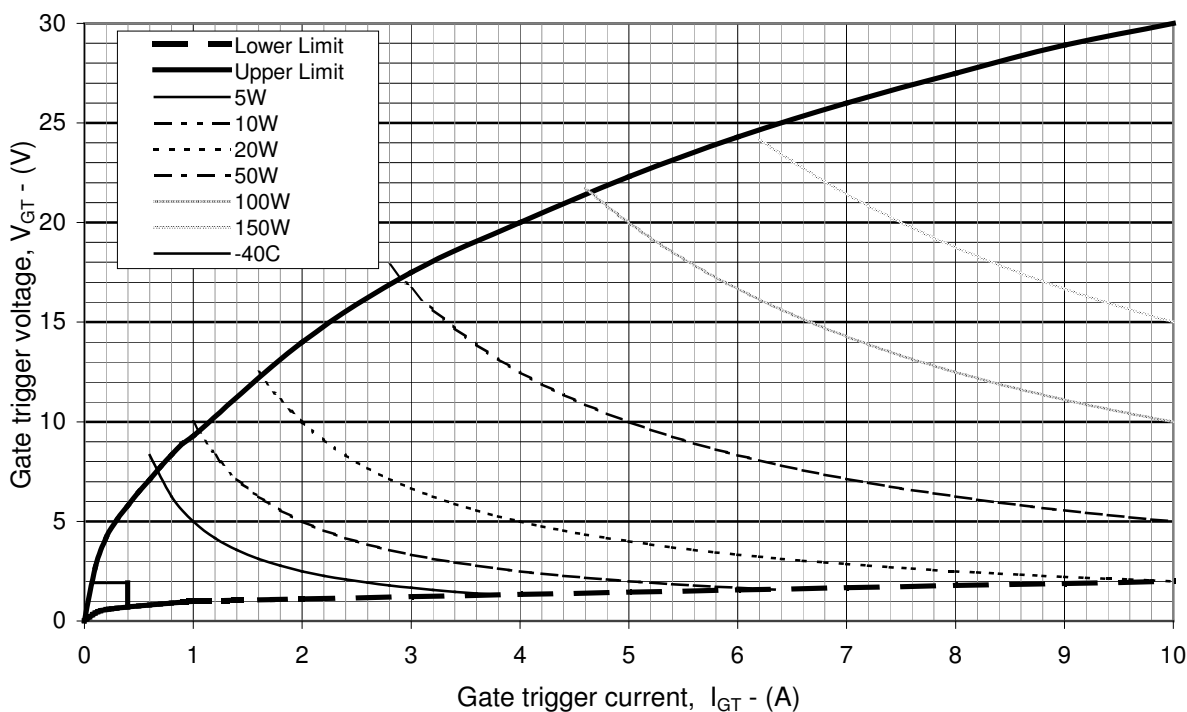
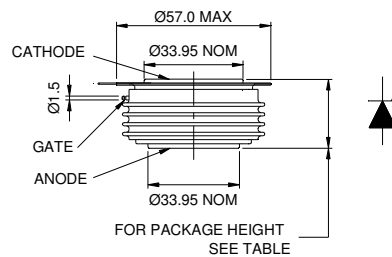
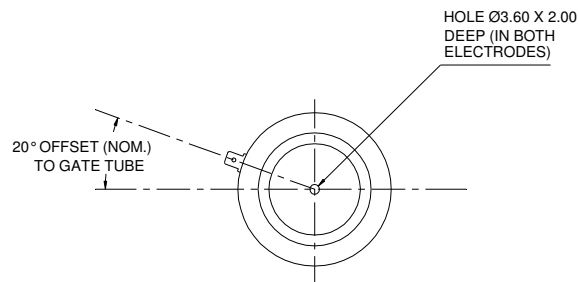


Fig. 13 Gate characteristics

PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

3rd ANGLE PROJECTION  DO NOT SCALE IF IN DOUBT ASK



Device	Maximum Thickness (mm)	Minimum Thickness (mm)
DCR803SG18	26.415	25.865
DCR806SG28	26.49	25.94
DCR818SG48	26.84	26.17
DCR820SG65	27.1	26.55
DCR1080G22	26.415	25.865
DCR960G28	26.49	25.94
DCR780G42	26.72	26.17
DCR690G52	26.84	26.29
DCR590G65	27.1	26.55
DCR470G85	27.46	26.91

Clamping force: 11.5 kN $\pm$ 10%
Lead length: 420mm
Lead terminal connector: M4 ring

Package outline type code: G

Fig.14 Package outline

POWER ASSEMBLY CAPABILITY

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink and clamping systems in line with advances in device voltages and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group offers high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the latest CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete Solution (PACs).

HEATSINKS

The Power Assembly group has its own proprietary range of extruded aluminium heatsinks which have been designed to optimise the performance of Dynex semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest sales representative or Customer Services.

Stresses above those listed in this data sheet may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed.



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